

Description:

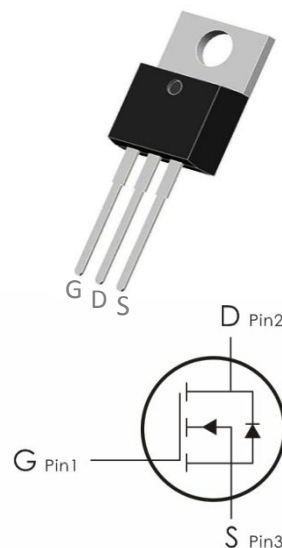
This N-Channel MOSFET uses advanced SGT technology and

design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=100V, I_D=15A, R_{DS(ON)} < 75m\Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(ON)}$.
- 5) Excellent package for good heat dissipation.



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DOP15N10T	15N10T	TO- 220	50 pcs/Tube

Absolute Maximum Ratings: ($T_C=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Curren ¹	15	A
I_{DM}	Pulsed Drain Current ²	55	
P_D	Power Dissipation	44	W
E_{AS}	Single pulse avalanche energy ⁵	8.5	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^{\circ}C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.84	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	62	$^{\circ}C/W$

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourctce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	100	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =100V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	1.2	---	2.5	V
R _{DS(ON)}	Drain-Source On Resistance	V _{GS} =10V, I _D =5A	---	50	75	m Ω
		V _{GS} =4.5V, I _D =3A	---	60	90	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	---	309	---	pF
C _{oss}	Output Capacitance		---	170	--	
C _{rss}	Reverse Transfer Capacitance		---	16.6	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =50V, I _D =5A, V _{GS} =10V	---	13	---	ns
t _r	Rise Time		---	3.1	---	ns
t _{d(off)}	Turn-Off Delay Time		---	35	---	ns
t _f	Fall Time		---	13	---	ns
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =50V, I _D =5A	---	6.4	---	nc
Q _{gs}	Gate-Source Charge		---	1.3	---	nc
Q _{gd}	Gate-Drain “Miller” Charge		---	1.3	---	nc
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage ¹	V _{GS} =0V, I _{SD} =7A	---	---	1.3	V
I _S	Continuous Drain Curren ³	VD=VG=0V	---	---	15	A
I _{SM}	Pulsed Drain Current		---	---	55	A
Trr	Reverse Recovery Time	I _F =5A, T _J =25 °C	---	36	---	ns
Qrr	Reverse Recovery Charge	dI/dt=100A/us	---	37	---	nc

Notes:

1. Calculated continuous current based on maximum allowable junction temperature.
2. Repetitive rating; pulse width limited by max. junction temperature.
3. Pd is based on max. junction temperature, using junction-case thermal resistance.
4. in a still air environment with $T_a=25\text{ }^{\circ}\text{C}$.
5. $V_{DD}=30\text{ V}$, $V_{GS}=10\text{ V}$, $L=0.3\text{ mH}$, starting $T_j=25\text{ }^{\circ}\text{C}$.

Typical Characteristics: ($T_c=25\text{ }^{\circ}\text{C}$ unless otherwise noted)

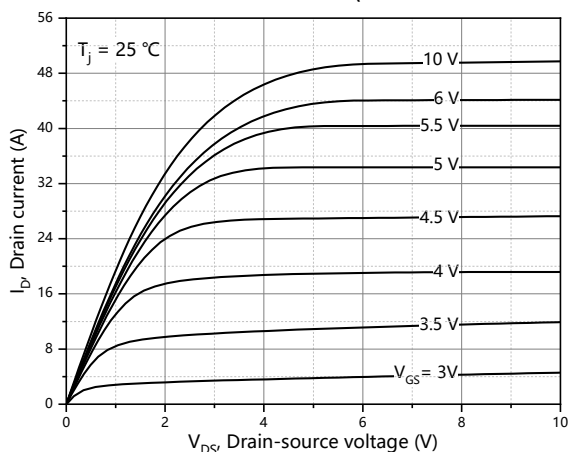


Figure 1. Typ. output characteristics

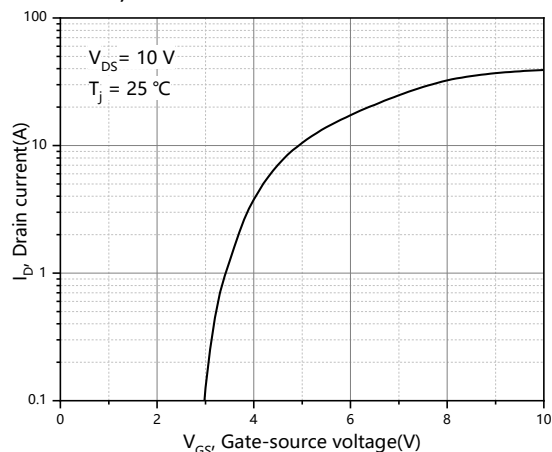


Figure 2. Typ. transfer characteristics

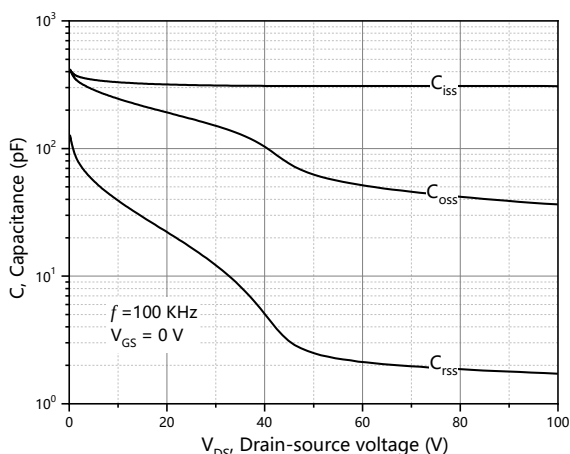


Figure 3. Typ. capacitances

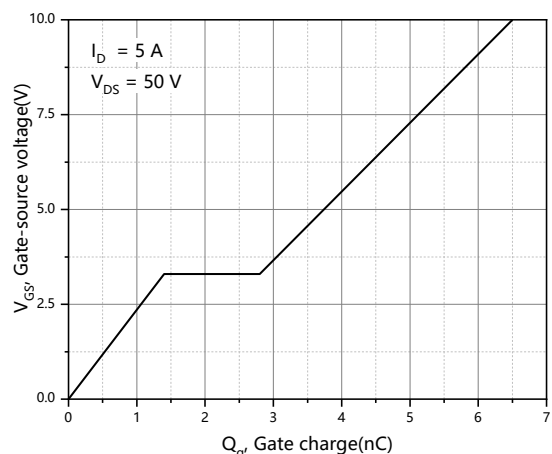


Figure 4. Typ. gate charge

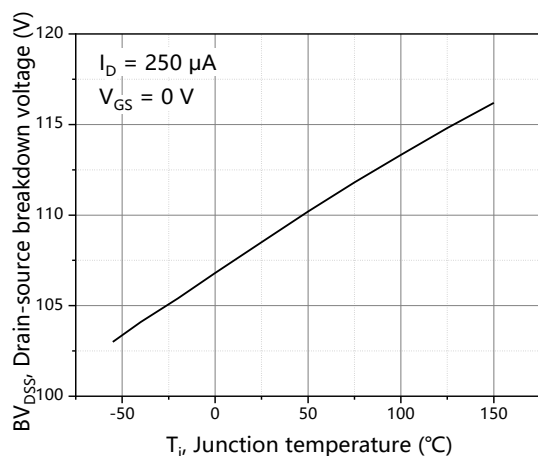


Figure 5. Drain-source breakdown voltage

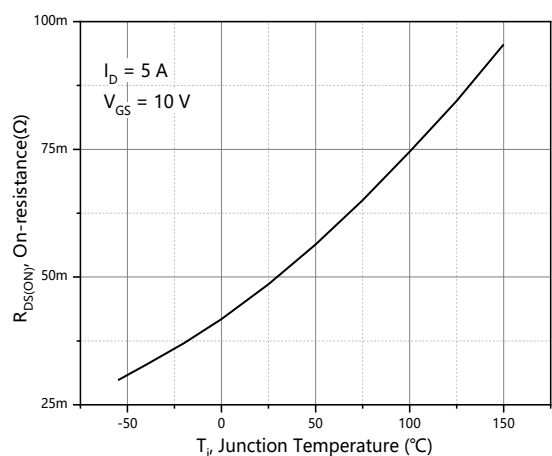


Figure 6. Drain-source on-state resistance

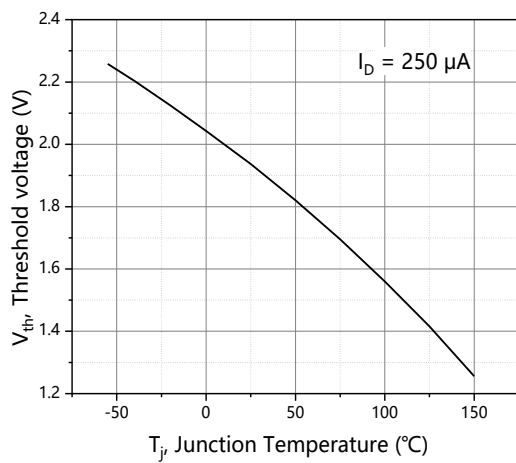


Figure 7. Threshold voltage

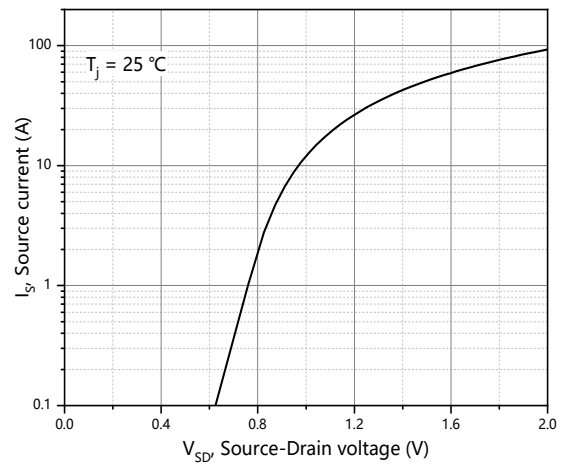


Figure 8. Forward characteristic of body diode

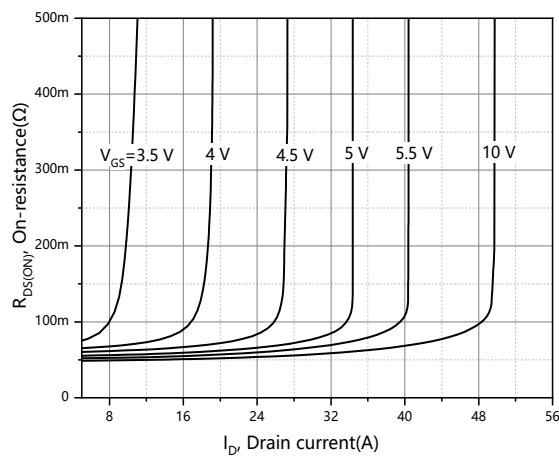


Figure 9. Drain-source on-state resistance

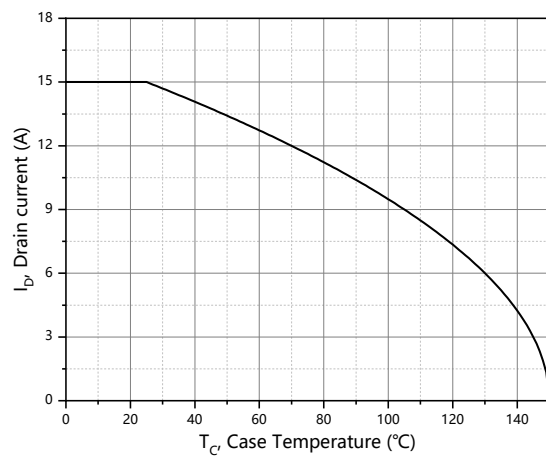
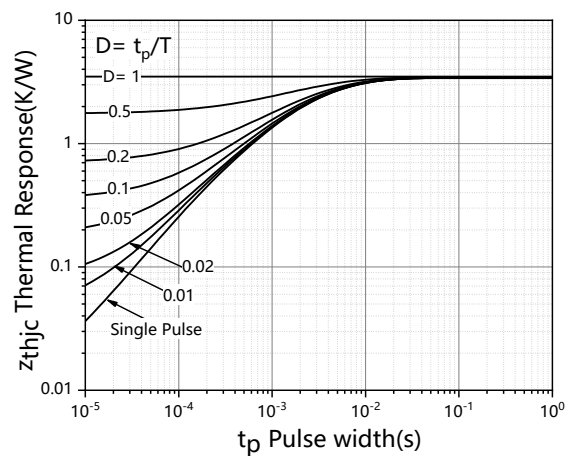
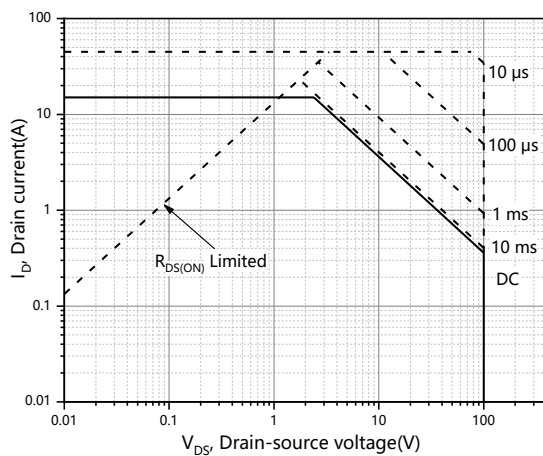
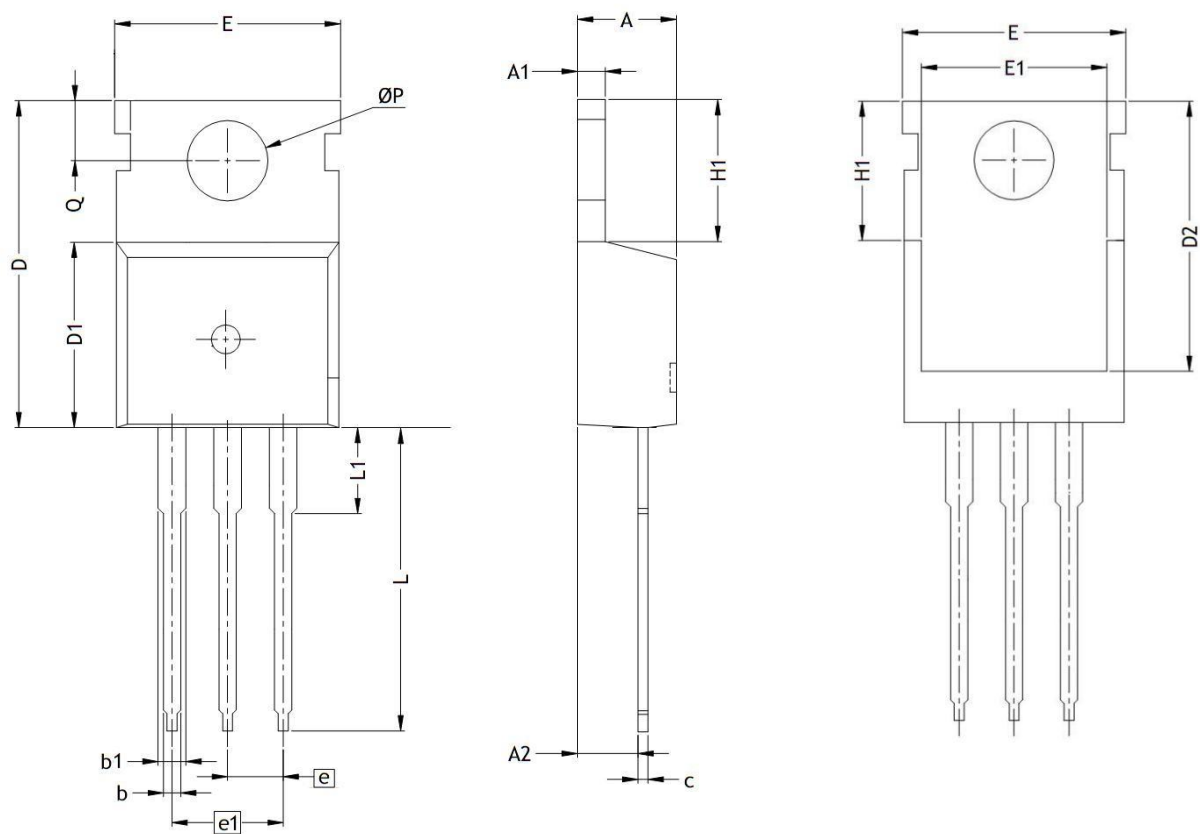


Figure 10. Drain current



TO-220 Package Information:



UNIT: mm

SYMBOLS	A	A1	A2	b	b1	c	D	D1	D2	E	E1	e
MIN	4.25	1.25	2.35	0.7	1.15	0.45	14.35	8.80	13.05	9.90	7.85	2.540
MAX	4.65	1.35	2.55	0.9	1.75	0.60	15.95	9.50	13.65	10.35	8.85	BSC
SYMBOLS	e1	H1	L	L1	Q	φP						
MIN	5.080	6.30	12.85	2.85	2.70	3.50						
MAX	BSC	6.65	13.50	3.25	2.90	3.70						

Marking Information:

①. Doingter LOGO

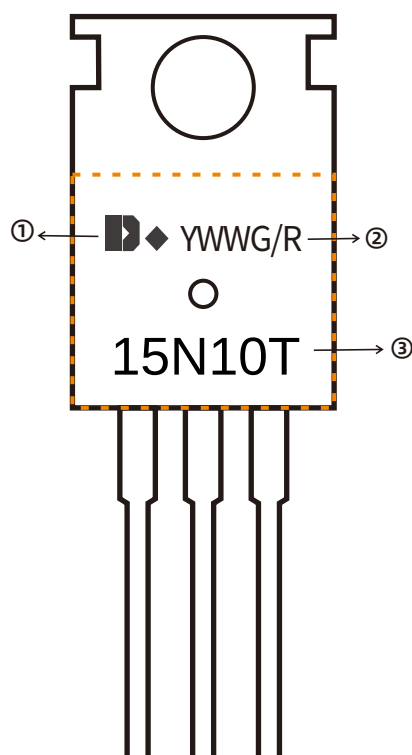
②. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)

③. Part NO.



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